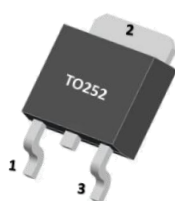


DESCRIPTION

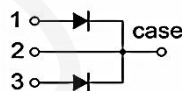
The MBR10150CT meet the ROHS and Green Product requirement with full function reliability approved.

FEATURE

- *Schottky Barrier Chip
- *Guard Ring Die Construction for Transient Protection
- *Low Power Loss,High Efficiency
- *High Surge Capability
- *High Current Capability and Low Forward Voltage Drop
- *For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



1. ANODE
2. CATHODE
3. ANODE



ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

SYMBOL	PARAMETER	VALUE	UNIT
VRRM	Peak repetitive reverse voltage	150	V
VRWM	Working peak reverse voltage	150	V
VR	DC blocking voltage	150	V
VR(RMS)	RMS reverse voltage	105	V
IO	Average rectified output current	10(5*2)	A
IFSM	Non-Repetitive peak forward surge current(8.3ms half sine wave)	100*2	A
Tj	Junction temperature	175	°C
Tstg	Storage temperature	-55~+150	°C
RθJA	Thermal Resistance from Junction to Ambient	100	°C/W
RθJC	Thermal Resistance From Junction To Case	6	°C/W

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Reverse voltage	V _(BR)	I _R =0.1mA		150			V
Reverse current	I _R	V _R =150V			1	5	μA
Forward voltage	V _{F1}	I _F =3A	T _j =25°C		0.75		V
	V _{F2}	I _F =5A	T _j =25°C		0.82	0.85	V
	V _{F3}	I _F =10A	T _j =25°C			0.95	V
Typical total capacitance	C _{tot}	V _R =5V, f=1MHz			500		pF

*Notes:1. Short duration on pulse test used to minimize self-heating effect.

2. Thermal resistance junction to case mounted on heatsink.
3. Pulse test pulse width ≤300μs, duty cycle≤2.0%.

■ TYPICAL CHARACTERISTICS

